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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patentee:	Ko, *et al.*	Docket No.:	TSM03-0615
Serial No.:	10/729,495	Art Unit:	2811
Patent No.:	7,112,495 B2	Issue Date:	September 26, 2006
Filed:	December 5, 2003	Examiner:	Hung K. Vu
For:	Structure and Method of a Strained Channel Transistor and a Second Semiconductor Component in an Integrated Circuit		

Certificate of Corrections Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Request for Issuance of Certificate of Correction Pursuant to 35 U.S.C. § 254 and 37 C.F.R. § 1.322

Dear Sir:

Upon review of the above-identified issued patent, Patentee notes errors in the patent that should be corrected as shown on the attached Certificate of Correction.

The mistakes noted on the attached Certificate of Correction were incurred through the fault of the Patent and Trademark Office. Accordingly, no fee is required.

Patentee respectfully solicits the issuance of the requested Certificate of Correction.

Respectfully submitted,

October 9, 2006
Date

Steven H. Slater
Attorney for Patentee
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PTO/SB/44 (04-05)
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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,112,495 B2

APPLICATION NO. : 10/729,095

ISSUE DATE : September 26, 2006

INVENTOR(S) : Ko, *et al.*

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, Column 1, line 65; delete "6,872,810" insert --6,872,610--
Page 2, Column 2, line 27; delete "TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, vol.49, No. 1, (Jan. 2002), pp.7-14." insert --TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique," Symposium On VLSI Technology Digest of Technial Papers, (2002), pp. 96-97.--
Column 5, line 6; delete "patent application" insert --Patent Application--
Column 6, line 24; delete "suicides" insert --silicides--
Column 17, line 2; delete "cobalt suicide" insert --cobalt silicide--
Column 17, line 2; delete "nickel suicide" insert --nickel silicide--
Column 17, line 40; delete "suicide" insert --silicide--
Column 17, line 42; delete "stank" insert --stack--

MAILING ADDRESS OF SENDER(Please do not use customer number below):

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Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))

Date of Deposit: October 9, 2006

I hereby certify that the below listed correspondence is being deposited with the United States Postal Service on the date indicated above as first class mail in an envelope addressed to: Certificate of Corrections Branch, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.

Certificate of Mailing via First Class Mail (1 page)
Request for Issuance of Certificate of Correction (1 page)
Certificate of Correction (1 original and 1 copy)
Return Postcard

Respectfully submitted,

Michelle Reyes

Michelle Reyes
Legal Assistant

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